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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	S08
Core Size	8-Bit
Speed	20MHz
Connectivity	I²C, SCI, SPI
Peripherals	LCD, LVD, POR, PWM, WDT
Number of I/O	38
Program Memory Size	10KB (10K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 8x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc9s08ll8clh

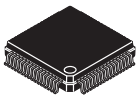
Freescale Semiconductor
Data Sheet: Technical Data

Document Number: MC9S08LL16
Rev. 7, 1/2013

An Energy Efficient Solution by Freescale

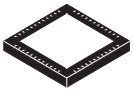
MC9S08LL16 Series

Covers: MC9S08LL16 and MC9S08LL8



64-LQFP
Case 840F

48-LQFP
Case 932



48-QFN
1314

Features

- 8-Bit HCS08 Central Processor Unit (CPU)
  - Up to 20-MHz CPU at 3.6V to 1.8V across temperature range of -40°C to 85°C
  - HC08 instruction set with added BGND instruction
  - Support for up to 32 interrupt/reset sources
- On-Chip Memory
  - Dual Array FLASH read/program/erase over full operating voltage and temperature
  - Random-access memory (RAM)
  - Security circuitry to prevent unauthorized access to RAM and FLASH contents
- Power-Saving Modes
  - Two low power stop modes
  - Reduced power wait mode
  - Low power run and wait modes allow peripherals to run while voltage regulator is in standby
  - Peripheral clock gating register can disable clocks to unused modules, thereby reducing currents.
  - Very low power external oscillator that can be used in stop2 or stop3 modes to provide accurate clock source to real time counter
  - 6 usec typical wake up time from stop3 mode
- Clock Source Options
  - Oscillator (XOSC) — Loop-control Pierce oscillator; Crystal or ceramic resonator range of 31.25 kHz to 38.4 kHz or 1 MHz to 16 MHz
  - Internal Clock Source (ICS) — Internal clock source module containing a frequency-locked-loop (FLL) controlled by internal or external reference; precision trimming of internal reference allows 0.2% resolution and 2% deviation over temperature and voltage; supports bus frequencies from 1MHz to 10 MHz.
- System Protection
  - Watchdog computer operating properly (COP) reset with option to run from dedicated 1-kHz internal clock source or bus clock
  - Low-Voltage Warning with interrupt
  - Low-Voltage Detection with reset or interrupt
  - Illegal opcode and illegal address detection with reset
  - Flash block protection
- Development Support
  - Single-wire background debug interface
  - Breakpoint capability to allow single breakpoint setting during in-circuit debugging (plus two more breakpoints in on-chip debug module)
  - On-chip in-circuit emulator (ICE) debug module containing three comparators and nine trigger modes. Eight deep FIFO for storing change-of-flow addresses and event-only data. Debug module supports both tag and force breakpoints
- Peripherals
  - **LCD** — 4x28 or 8x24 LCD driver with internal charge pump and option to provide an internally regulated LCD reference that can be trimmed for contrast control.
  - **ADC** — 8-channel, 12-bit resolution; 2.5 µs conversion time; automatic compare function; temperature sensor; internal bandgap reference channel; operation in stop3; fully functional from 3.6V to 1.8V
  - **ACMP** — Analog comparator with selectable interrupt on rising, falling, or either edge of comparator output; compare option to fixed internal bandgap reference voltage; outputs can be optionally routed to TPM module; operation in stop3
  - **SCI** — Full duplex non-return to zero (NRZ); LIN master extended break generation; LIN slave extended break detection; wake up on active edge
  - **SPI**— Full-duplex or single-wire bidirectional; Double-buffered transmit and receive; Master or Slave mode; MSB-first or LSB-first shifting
  - **IIC** — IIC with up to 100 kbps with maximum bus loading; Multi-master operation; Programmable slave address; Interrupt driven byte-by-byte data transfer; supports broadcast mode and 10-bit addressing
  - **TPMx** — Two 2-channel (TPM1 and TPM2); Selectable input capture, output compare, or buffered edge- or center-aligned PWM on each channel;
  - **TOD**— (Time Of Day) 8-bit quarter second counter with match register; External clock source for precise time base, time-of-day, calendar or task scheduling functions; Free running on-chip low power oscillator (1 kHz) for cyclic wake-up without external components.
- Input/Output
  - 38 GPIOs, 2 output-only pins
  - 8 KBI interrupts with selectable polarity
  - Hysteresis and configurable pull up device on all input pins; Configurable slew rate and drive strength on all output pins.
- Package Options
  - 64-LQFP, 48-LQFP and 48-QFN

1 Devices in the MC9S08LL16 Series

Table 1 summarizes the feature set available in the MC9S08LL16 series of MCUs.

Table 1. MC9S08LL16 Series Features by MCU and Package

Feature	MC9S08LL16		MC9S08LL8
Package	64-pin LQFP	48-pin QFN/LQFP	48-pin QFN/LQFP
FLASH	16,384 (Dual 8K Arrays)		10,240 (8K and 2K arrays)
RAM	2080	2080	2080
ACMP	yes	yes	yes
ADC	8-ch	8-ch	8-ch
IIC	yes	yes	yes
IRQ	yes	yes	yes
KBI	8	8	8
SCI	yes	yes	yes
SPI	yes	yes	yes
TPM1	2-ch	2-ch	2-ch
TPM2	2-ch	-	-
TOD	Yes	Yes	Yes
LCD	8x24 4x28	8x16 4x20	8x16 4x20
I/O pins[1]	38	31	31

1 I/O does not include two output-only port pins.

The block diagram in Figure 1 shows the structure of the MC9S08LL16 series MCU.

Table 2. Pin Availability by Package Pin-Count

		<-- Lowest **Priority** --> Highest				
64	**48**	**Port Pin**	**Alt 1**	**Alt 2**	**Alt3**	**Alt4**
1	47	PTE1	LCD9			
2	48	PTE0	LCD8			
3	1	PTD7	LCD7			
4	2	PTD6	LCD6			
5	3	PTD5	LCD5			
6	4	PTD4	LCD4			
7	5	PTD3	LCD3			
8	6	PTD2	LCD2			
9	7	PTD1	LCD1			
10	8	PTD0	LCD0			
11	9		V_{cap1}			
12	10		V_{cap2}			
13	11		V_{LL1}			
14	12		V_{LL2}			
15	13		V_{LL3}			
16	—		V_{LCD}			
17	14	PTA6	KBIP6	ADP6	ACMP+	
18	15	PTA7	KBIP7	ADP7	ACMP–	
19	16				V_{SSA}	
					V_{REFL}	
20	17				V_{REFH}	
					V_{DDA}	
21	18	PTB0		EXTAL		
22	19	PTB1		XTAL		
23	20				V_{DD}	
24	21				V_{SS}	
25	22	PTB2	$\overline{\text{RESET}}$			
26	—	PTB3				
27	—	PTB4	—	MISO	SDA	
28	—	PTB5	—	MOSI	SCL	
29	—	PTB6	—	SPSCK		
30	—	PTB7	—	$\overline{\text{SS}}$		
31	23	PTC0		RxD		
32	24	PTC1		TxD		
33	25	PTC2		TPM1CH0		
34	26	PTC3		TPM1CH1		
35	—	PTC4		TPM2CH0		
36	—	PTC5		TPM2CH1		
37	27	PTC6	ACMPO	BKGD	MS	
38	28	PTC7		IRQ	TCLK	
39	29	PTA0	KBIP0	—	$\overline{\text{SS}}$	ADP0

Table 2. Pin Availability by Package Pin-Count (continued)

		<-- Lowest **Priority** --> Highest				
64	**48**	**Port Pin**	**Alt 1**	**Alt 2**	**Alt3**	**Alt4**
40	30	PTA1	KBIP1	—	SPSCK	ADP1
41	31	PTA2	KBIP2	SDA	MISO	ADP2
42	32	PTA3	KBIP3	SCL	MOSI	ADP3
43	33	PTA4	KBIP4	ADP4	LCD31	
44	34	PTA5	KBIP5	ADP5	LCD30	
45	35		LCD29			
46	36		LCD28			
47	37		LCD27			
48	38		LCD26			
49	39		LCD25			
50	40		LCD24			
51	—		LCD23			
52	—		LCD22			
53	—		LCD21			
54	—		LCD20			
55			LCD19			
56			LCD18			
57			LCD17			
58			LCD16			
59	41	PTE7	LCD15			
60	42	PTE6	LCD14			
61	43	PTE5	LCD13			
62	44	PTE4	LCD12			
63	45	PTE3	LCD11			
64	46	PTE2	LCD10			

3 Electrical Characteristics

3.1 Introduction

This section contains electrical and timing specifications for the MC9S08LL16 series of microcontrollers available at the time of publication.

3.2 Parameter Classification

The electrical parameters shown in this supplement are guaranteed by various methods. To give the customer a better understanding the following classification is used and the parameters are tagged accordingly in the tables where appropriate:

Table 3. Parameter Classifications

P	Those parameters are guaranteed during production testing on each individual device.
C	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
T	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

NOTE

The classification is shown in the column labeled “C” in the parameter tables where appropriate.

3.3 Absolute Maximum Ratings

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in Table 4 may affect device reliability or cause permanent damage to the device. For functional operating conditions, refer to the remaining tables in this section.

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (for instance, either V_{SS} or V_{DD}) or the programmable pull-up resistor associated with the pin is enabled.

Table 4. Absolute Maximum Ratings

Rating	Symbol	Value	Unit
Supply voltage	V_{DD}	–0.3 to 3.8	V
Maximum current into V_{DD}	I_{DD}	120	mA
Digital input voltage	V_{In}	–0.3 to V_{DD} + 0.3	V
Instantaneous maximum current Single pin limit (applies to all port pins)[1, 2, 3]	I_D	± 25	mA
Storage temperature range	T_{stg}	–55 to 150	°C

1 Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive (V_{DD}) and negative (V_{SS}) clamp voltages, then use the larger of the two resistance values.

2 All functional non-supply pins, except for PTB2 are internally clamped to V_{SS} and V_{DD}.

3 Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current ($V_{In} > V_{DD}$) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if the clock rate is very low (which would reduce overall power consumption).

3.4 Thermal Characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in on-chip logic and voltage regulator circuits, and it is user-determined rather than being controlled by the MCU design. To take $P_{I/O}$ into account in power calculations, determine the difference between actual pin voltage and V_{SS} or V_{DD} and multiply by the pin current for each I/O pin. Except in cases of unusually high pin current (heavy loads), the difference between pin voltage and V_{SS} or V_{DD} will be very small.

Table 5. Thermal Characteristics

Rating	Symbol	Value	Unit
Operating temperature range (packaged)	T_A	T_L to T_H –40 to 85	°C
Maximum junction temperature	T_{JM}	95	°C
Thermal resistance Single-layer board			
64-pin LQFP	θ_{JA}	72	°C/W
48-pin QFN		84	
48-pin LQFP		81	
Thermal resistance Four-layer board			
64-pin LQFP	θ_{JA}	54	°C/W
48-pin QFN		30	
48-pin LQFP		57	

The average chip-junction temperature (T_J) in °C can be obtained from:

$$T_J = T_A + (P_D \times \theta_{JA}) \qquad \textit{Eqn. 3-1}$$

where:

T_A = Ambient temperature, °C
θ_{JA} = Package thermal resistance, junction-to-ambient, °C/W
$P_D = P_{int} + P_{I/O}$
$P_{int} = I_{DD} \times V_{DD}$, Watts — chip internal power
$P_{I/O}$ = Power dissipation on input and output pins — user determined

For most applications, $P_{I/O} << P_{int}$ and can be neglected. An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is:

$$P_D = K \div (T_J + 273°C) \qquad \textit{Eqn. 3-2}$$

Solving Equation 3-1 and Equation 3-2 for K gives:

$$K = P_D \times (T_A + 273°C) + \theta_{JA} \times (P_D)^2 \qquad \textit{Eqn. 3-3}$$

Table 8. DC Characteristics (continued)

Num	C	Characteristic		Symbol	Condition	Min	Typ[1]	Max	Unit
11	P	Input leakage current	all input only pins except for LCD only pins (LCD 16-29)	$\|I_{In}\|$	$V_{In} = V_{DD}$	—	0.025	1	μA
					$V_{In} = V_{SS}$	—	0.025	1	μA
			LCD only pins (LCD 16-29)		$V_{In} = V_{DD}$	—	100	150	μA
					$V_{In} = V_{SS}$	—	0.025	1	μA
12	P	Hi-Z (off-state) leakage current	all input/output (per pin)	$\|I_{OZ}\|$	$V_{In} = V_{DD}$ or V_{SS}	—	0.025	1	μA
13	P	Total leakage current[3]	Total leakage current for all pins	$\|I_{InT}\|$	$V_{In} = V_{DD}$ or V_{SS}	—	—	2	μA
14	P	Pullup, pulldown resistors when enabled	PTA[0:3], PTA[6:7], PTB[0:7], PTC[0:7]	R_{PU}, R_{PD}	—	17.5	—	52.5	kΩ
	P		PTA[4:5], PTD[0:7], PTE[0:7]					69.5	
15	D	DC injection current [4, 5, 6]	Single pin limit	I_{IC}	$V_{IN} < V_{SS}$, $V_{IN} > V_{DD}$	–0.2	—	0.2	mA
			Total MCU limit, includes sum of all stressed pins			–5	—	5	mA
16	C	Input capacitance, all pins		C_{In}		—	—	8	pF
17	C	RAM retention voltage		V_{RAM}		—	0.6	1.0	V
18	C	POR re-arm voltage[7]		V_{POR}		0.9	1.4	2.0	V
19	D	POR re-arm time		t_{POR}		10	—	—	μs
20	P	Low-voltage detection threshold		V_{LVD}	V_{DD} falling V_{DD} rising	1.80 1.88	1.84 1.92	1.88 1.96	V
21	P	Low-voltage warning threshold		V_{LVW}	V_{DD} falling V_{DD} rising	2.08	2.14	2.2	V
22	P	Low-voltage inhibit reset/recover hysteresis		V_{hys}		—	80	—	mV
23	P	Bandgap voltage reference[8]		V_{BG}		1.15	1.17	1.18	V

1 Typical values are measured at 25 °C. Characterized, not tested

2 All I/O pins except for LCD pins in open drain mode.

3 Total leakage current is the sum value for all GPIO pins. This leakage current is not distributed evenly across all pins but characterization data shows that individual pin leakage current maximums are less than 250 nA.

4 All functional non-supply pins, except for PTB2 are internally clamped to V_{SS} and V_{DD}.

5 Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the larger of the two values.

6 Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If the positive injection current ($V_{In} > V_{DD}$) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure that external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if clock rate is very low (which would reduce overall power consumption).

7 POR will occur below the minimum voltage.

8 Factory trimmed at V_{DD} = 3.0 V, Temp = 25 °C.

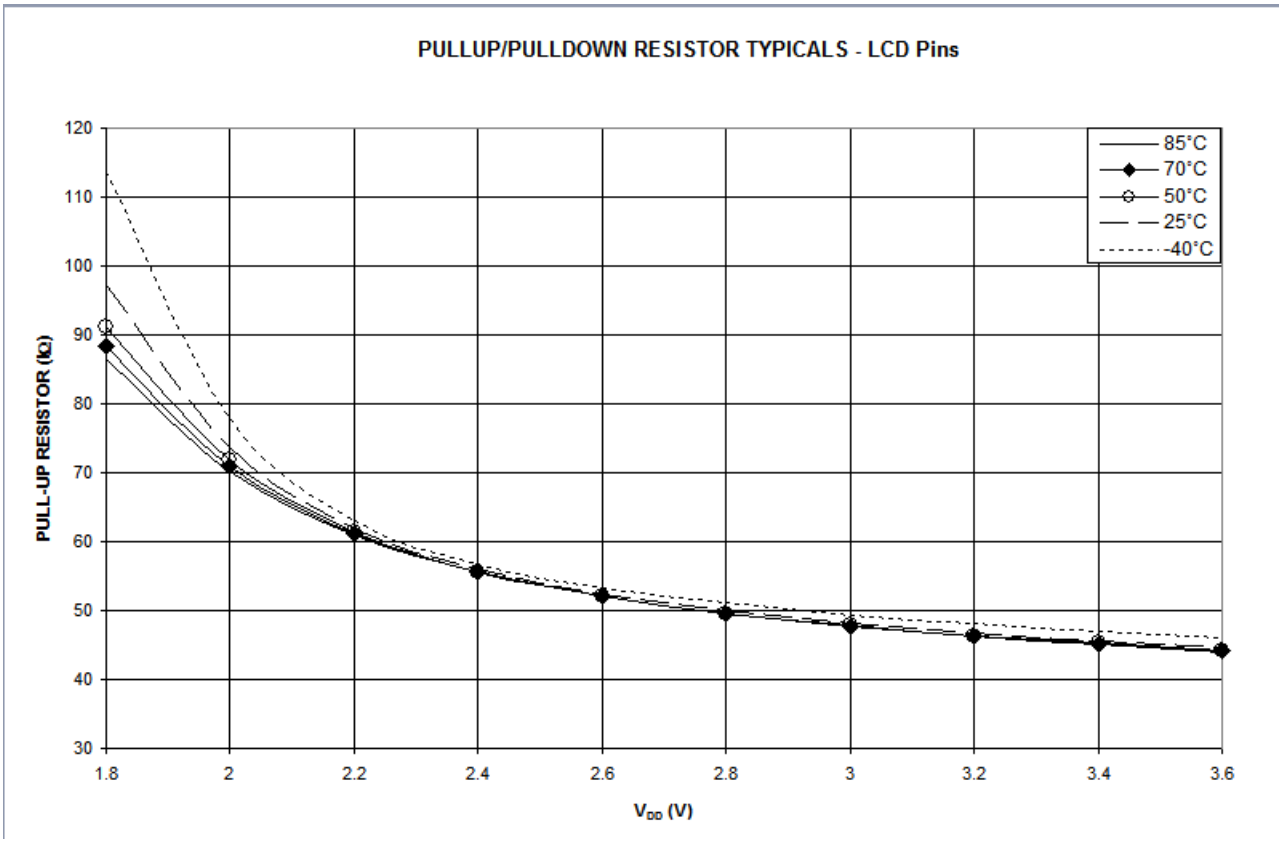


Figure 5. LCD/GPIO Pins I/O Pullup/Pulldown Typical Resistor Values

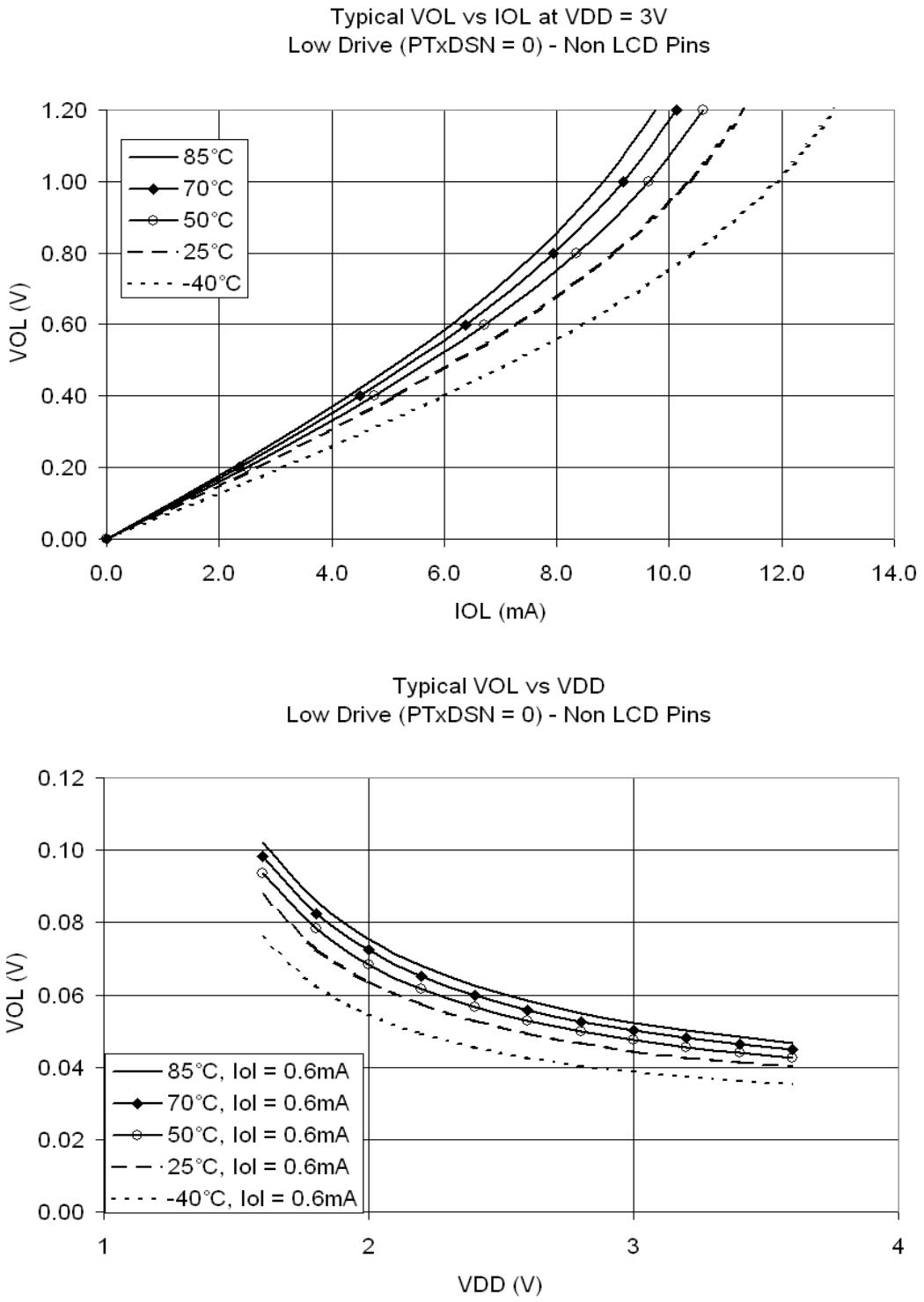


Figure 6. Typical Low-Side Driver (Sink) Characteristics (Non-LCD pins) — Low Drive (PTxDSn = 0)

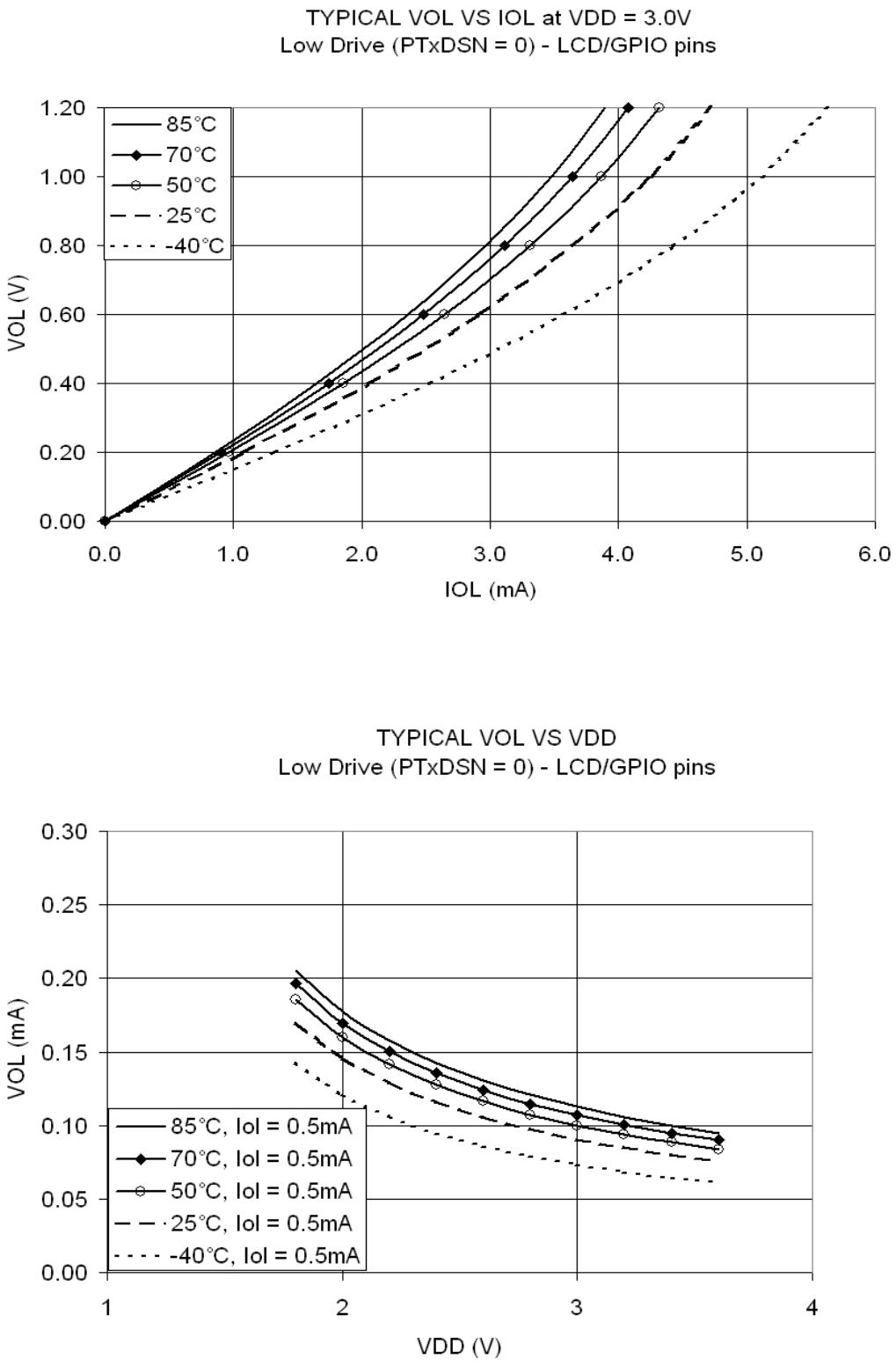


Figure 10. Typical Low-Side Driver (Sink) Characteristics (LCD/GPIO Pins) — Low Drive (PTxDSn = 0)

Table 12. ICS Frequency Specifications (Temperature Range = –40 to 85°C Ambient) (continued)

Num	C	Characteristic	Symbol	Min	Typ[1]	Max	Unit
9	C	Total deviation from trimmed DCO output frequency over fixed voltage and temperature range of 0°C to 70 °C	Δf_{dco_t}	—	±0.5	±1	$\%f_{dco}$
10	C	FLL acquisition time [2]	$t_{Acquire}$	—	—	1	ms
11	C	Long term jitter of DCO output clock (averaged over 2-ms interval) [3]	C_{Jitter}	—	0.02	0.2	$\%f_{dco}$

1 Data in Typical column was characterized at 3.0 V, 25 °C or is typical recommended value.

2 This specification applies to any time the FLL reference source or reference divider is changed, trim value changed or changing from FLL disabled (FBELP, FBILP) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

3 Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum f_{Bus}. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the FLL circuitry via V_{DD} and V_{SS} and variation in the crystal oscillator frequency increase the C_{Jitter} percentage for a given interval.

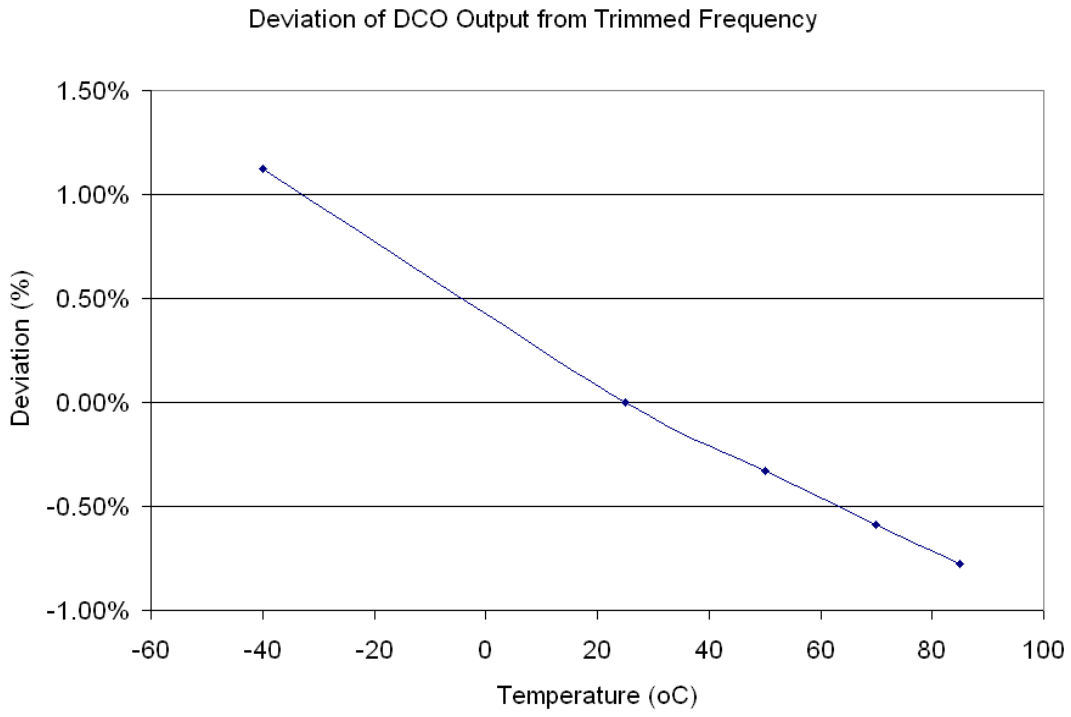


Figure 16. Deviation of DCO Output from Trimmed Frequency (20 MHz, 3.0 V)

3.10 AC Characteristics

This section describes timing characteristics for each peripheral system.

3.10.1 Control Timing

Table 13. Control Timing

Num	C	Rating	Symbol	Min	Typ[1]	Max	Unit
1	D	Bus frequency ($t_{cyc} = 1/f_{Bus}$)	f_{Bus}	dc	—	10	MHz
2	D	Internal low power oscillator period	t_{LPO}	700	—	1300	μs
3	D	External reset pulse width[2]	t_{extrst}	100	—	—	ns
4	D	Reset low drive	t_{rstdrv}	$34 \times t_{cyc}$	—	—	ns
5	D	BKGD/MS setup time after issuing background debug force reset to enter user or BDM modes	t_{MSSU}	500	—	—	ns
6	D	BKGD/MS hold time after issuing background debug force reset to enter user or BDM modes [3]	t_{MSH}	100	—	—	μs
7	D	IRQ pulse width Asynchronous path[2] Synchronous path[4]	t_{ILIH}, t_{IHIL}	 100 $1.5 \times t_{cyc}$	 — —	 — —	ns
8	D	Keyboard interrupt pulse width Asynchronous path[2] Synchronous path[4]	t_{ILIH}, t_{IHIL}	 100 $1.5 \times t_{cyc}$	 — —	 — —	ns
9	C	Port rise and fall time — Non-LCD Pins Low output drive (PTxDS = 0) (load = 50 pF)[5, 6] Slew rate control disabled (PTxSE = 0) Slew rate control enabled (PTxSE = 1)	t_{Rise}, t_{Fall}	 — —	 16 23	 — —	ns
		Port rise and fall time — Non-LCD Pins High output drive (PTxDS = 1) (load = 50 pF)[5, 6] Slew rate control disabled (PTxSE = 0) Slew rate control enabled (PTxSE = 1)	t_{Rise}, t_{Fall}	 — —	 5 9	 — —	ns
10	C	Voltage Regulator Recovery time	t_{VRR}	—	6	10	us

1 Typical values are based on characterization data at V_{DD} = 3.0 V, 25 °C unless otherwise stated.

2 This is the shortest pulse that is guaranteed to be recognized as a reset pin request.

3 To enter BDM mode following a POR, BKGD/MS should be held low during the power-up and for a hold time of t_{MSH} after V_{DD} rises above V_{LVD}.

4 This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In stop mode, the synchronizer is bypassed so shorter pulses can be recognized.

5 Timing is shown with respect to 20% V_{DD} and 80% V_{DD} levels. Temperature range –40 °C to 85 °C.

6 Except for LCD pins in Open Drain mode.

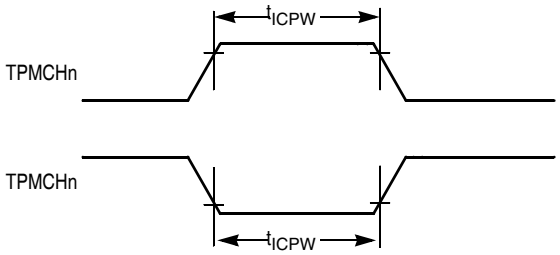


Figure 20. Timer Input Capture Pulse

3.10.3 SPI Timing

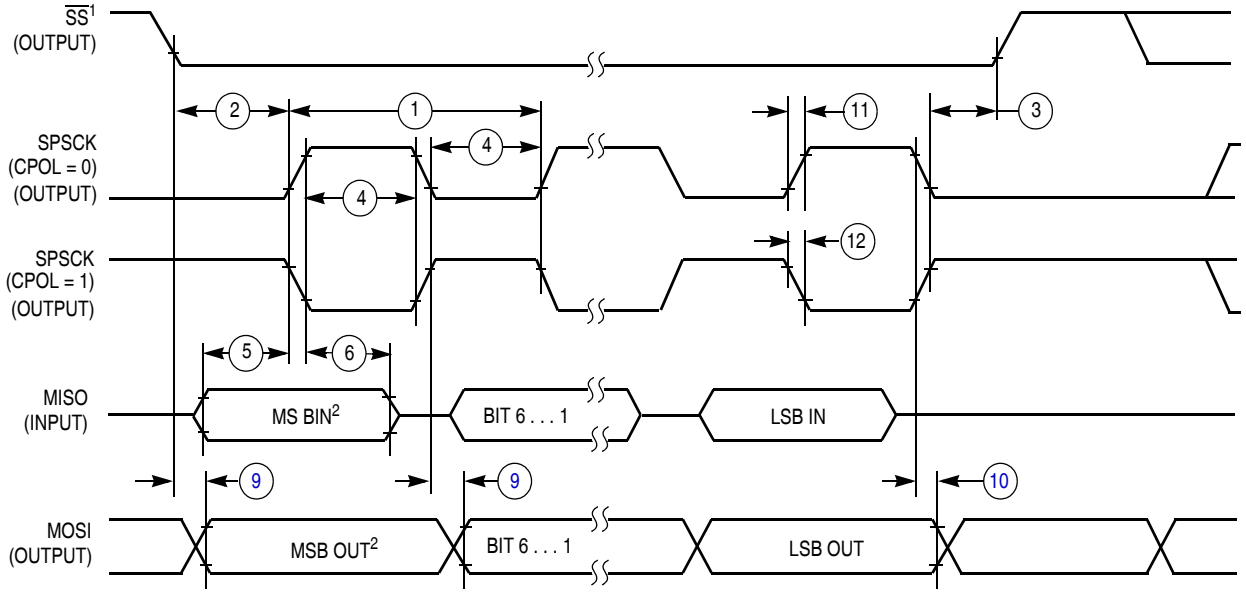
Table 15 and Figure 21 through Figure 24 describe the timing requirements for the SPI system.

Table 15. SPI Timing

No.	C	Function	Symbol	Min	Max	Unit
—	D	Operating frequency Master Slave	f_{op}	$f_{Bus}/2048$ 0	$f_{Bus}/2$ $f_{Bus}/4$	Hz
①	D	SPSCK period Master Slave	t_{SPSCK}	2 4	2048 —	t_{cyc} t_{cyc}
②	D	Enable lead time Master Slave	t_{Lead}	1/2 1	— —	t_{SPSCK} t_{cyc}
③	D	Enable lag time Master Slave	t_{Lag}	1/2 1	— —	t_{SPSCK} t_{cyc}
④	D	Clock (SPSCK) high or low time Master Slave	t_{WSPSCK}	$t_{cyc} - 30$ $t_{cyc} - 30$	1024 t_{cyc} —	ns ns
⑤	D	Data setup time (inputs) Master Slave	t_{SU}	15 15	— —	ns ns
⑥	D	Data hold time (inputs) Master Slave	t_{HI}	0 25	— —	ns ns
⑦	D	Slave access time	t_a	—	1	t_{cyc}
⑧	D	Slave MISO disable time	t_{dis}	—	1	t_{cyc}
⑨	D	Data valid (after SPSCK edge) Master Slave	t_v	— —	25 25	ns ns

Table 15. SPI Timing (continued)

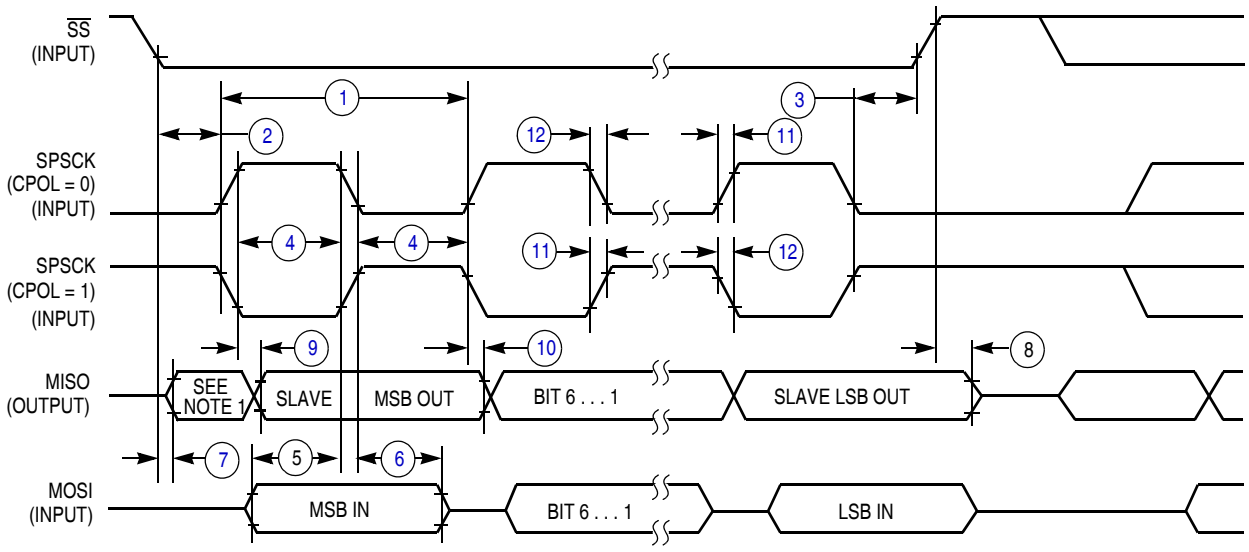
No.	C	Function	Symbol	Min	Max	Unit
⑩	D	Data hold time (outputs) Master Slave	t_{HO}	 0 0	 — —	 ns ns
⑪	D	Rise time Input Output	 t_{RI} t_{RO}	 — —	 t_{cyc} – 25 25	 ns ns
⑫	D	Fall time Input Output	 t_{FI} t_{FO}	 — —	 t_{cyc} – 25 25	 ns ns



NOTES:

1. SS output mode (DDS7 = 1, SSOE = 1).
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 21. SPI Master Timing (CPHA = 0)



NOTE:
1. Not defined but normally LSB of character just received.

Figure 24. SPI Slave Timing (CPHA = 1)

3.11 Analog Comparator (ACMP) Electricals

Table 16. Analog Comparator Electrical Specifications

C	Characteristic	Symbol	Min	Typical	Max	Unit
D	Supply voltage	V_{DD}	1.8	—	3.6	V
C	Supply current (active)	I_{DDAC}	—	20	35	µA
D	Analog input voltage	V_{AIN}	V_{SS} – 0.3	—	V_{DD}	V
P	Analog input offset voltage	V_{AIO}		20	40	mV
C	Analog comparator hysteresis	V_H	3.0	9.0	15.0	mV
P	Analog input leakage current	I_{ALKG}	—	—	1.0	µA
C	Analog comparator initialization delay	t_{AINIT}	—	—	1.0	µs

3.12 ADC Characteristics

Table 17. 12-bit ADC Operating Conditions

Characteristic	Conditions	Symb	Min	Typ[1]	Max	Unit	Comment
Supply voltage	Absolute	V_{DDA}	1.8	—	3.6	V	
	Delta to V_{DD} (V_{DD}–V_{DDA})[2]	ΔV_{DDA}	–100	0	100	mV	
Ground voltage	Delta to V_{SS} (V_{SS}–V_{SSA})[2]	ΔV_{SSA}	–100	0	100	mV	

Table 18. 12-bit ADC Characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA})

C	Characteristic	Conditions	Symb	Min	Typ[1]	Max	Unit	Comment
T	Supply Current ADLPC=1 ADLSMP=1 ADCO=1		I_{DDA}	—	120	—	μA	
T	Supply Current ADLPC=1 ADLSMP=0 ADCO=1		I_{DDA}	—	200	—	μA	
T	Supply Current ADLPC=0 ADLSMP=1 ADCO=1		I_{DDA}	—	290	—	μA	
P	Supply Current ADLPC=0 ADLSMP=0 ADCO=1		I_{DDA}	—	0.53	1	mA	
P	ADC Asynchronous Clock Source	High Speed (ADLPC=0)	f_{ADACK}	2	3.3	5	MHz	t_{ADACK} = $1/f_{ADACK}$
C		Low Power (ADLPC=1)		1.25	2	3.3		
P	Conversion Time (Including sample time)	Short Sample (ADLSMP=0)	t_{ADC}	—	20	—	ADCK cycles	See ADC chapter in the LL16 Reference Manual for conversion time variances
C		Long Sample (ADLSMP=1)		—	40	—		
P	Sample Time	Short Sample (ADLSMP=0)	t_{ADS}	—	3.5	—	ADCK cycles	
C		Long Sample (ADLSMP=1)		—	23.5	—		
T	Total Unadjusted Error	12-bit mode, 3.6>VDDA>2.7V	E_{TUE}	—	–1 to 3	–2.5 to 5.5	LSB[2]	Includes quantization
		12-bit mode, 2.7>VDDA>1.8V		—	–1 to 3	–3.0 to 6.0		
P		10-bit mode		—	±1	±2.5		
T		8-bit mode		—	±0.5	±1.0		
T	Differential Non-Linearity	12-bit mode	DNL	—	±1	–1.5 to 2.0	LSB[2]	
P		10-bit mode[3]		—	±0.5	±1.0		
T		8-bit mode[3]		—	±0.3	±0.5		
T	Integral Non-Linearity	12-bit mode	INL	—	±1.5	–2.5 to 1.0	LSB[2]	
P		10-bit mode		—	±0.5	±1.0		
T		8-bit mode		—	±0.3	±0.5		

3.13 LCD Specifications

Table 19. LCD Electricals, 3 V Glass

C	Characteristic		Symbol	Min	Typ	Max	Unit
D	LCD Supply Voltage		V_{LCD}	0.9	1.5	1.8	V
D	LCD Frame Frequency		f_{Frame}	28	30	58	Hz
D	LCD Charge Pump Capacitance		C_{LCD}		100	100	nF
D	LCD Bypass Capacitance		C_{BYLCD}		100	100	nF
D	LCD Glass Capacitance		C_{glass}		2000	8000	pF
D	V_{IREG}	HRefSel = 0 HRefSel = 1	V_{IREG}	.89 1.49	1.00 1.67	1.15 1.85[1]	V
D	V_{IREG} TRIM Resolution		Δ_{RTRIM}	1.5			% V_{IREG}
D	V_{IREG} Ripple	HRefSel = 0 HRefSel = 1				0.1 0.15	V
D	V_{LCD} Buffered Adder[2]		I_{Buff}		1		µA

1 V_{IREG} Max can not exceed V_{DD} – 0.15 V

2 VSUPPLY = 10, BYPASS = 0

3.14 Flash Specifications

This section provides details about program/erase times and program-erase endurance for the flash memory.

Program and erase operations do not require any special power sources other than the normal V_{DD} supply. For more detailed information about program/erase operations, see the Memory section.

Table 20. Flash Characteristics

C	Characteristic	Symbol	Min	Typical	Max	Unit
D	Supply voltage for program/erase -40°C to 85°C	$V_{prog/erase}$	1.8		3.6	V
D	Supply voltage for read operation	V_{Read}	1.8		3.6	V
D	Internal FCLK frequency[1]	f_{FCLK}	150		200	kHz
D	Internal FCLK period (1/FCLK)	t_{Fcyc}	5		6.67	µs
P	Byte program time (random location)[2]	t_{prog}	9			t_{Fcyc}
P	Byte program time (burst mode)[2]	t_{Burst}	4			t_{Fcyc}
P	Page erase time[2]	t_{Page}	4000			t_{Fcyc}
P	Mass erase time[2]	t_{Mass}	20,000			t_{Fcyc}
D	Byte program current[3]	RI_{DDBP}	—	4	—	mA
D	Page erase current[3]	RI_{DDPE}	—	6	—	mA
C	Program/erase endurance[4] T_L to T_H = –40°C to + 85°C T = 25°C		10,000	— 100,000	— —	cycles
C	Data retention[5]	t_{D_ret}	15	100	—	years

1 The frequency of this clock is controlled by a software setting.

2 These values are hardware state machine controlled. User code does not need to count cycles. This information supplied for calculating approximate time to program and erase.

3 The program and erase currents are additional to the standard run I_{DD}. These values are measured at room temperatures with V_{DD} = 3.0 V, bus frequency = 4.0 MHz.

4 Typical endurance for FLASH was evaluated for this product family on the 9S12Dx64. For additional information on how Freescale defines typical endurance, please refer to Engineering Bulletin EB619, *Typical Endurance for Nonvolatile Memory.*

5 Typical data retention values are based on intrinsic capability of the technology measured at high temperature and de-rated to 25°C using the Arrhenius equation. For additional information on how Freescale defines typical data retention, please refer to Engineering Bulletin EB618, *Typical Data Retention for Nonvolatile Memory.*

3.15 EMC Performance

Electromagnetic compatibility (EMC) performance is highly dependant on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components as well as MCU software operation all play a significant role in EMC performance. The system designer should consult Freescale applications notes such as AN2321, AN1050, AN1263, AN2764, and AN1259 for advice and guidance specifically targeted at optimizing EMC performance.

3.15.1 Radiated Emissions

Microcontroller radiated RF emissions are measured from 150 kHz to 1 GHz using the TEM/GTEM Cell method in accordance with the IEC 61967-2 and SAE J1752/3 standards. The measurement is performed with the microcontroller installed on a custom EMC evaluation board while running specialized EMC test software. The radiated emissions from the microcontroller are measured in a TEM cell in two package orientations (North and East).

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